Figure 8 - RHEED patterns and STM images of Si:H surfaces obtained as a result of different chemical treatments:

(a)–(c) after hydrogenation in dilute HF; (d)–(f) after hydrogenation in buffered HF + NH$_4$F; RHEED patterns: $E = 10$ keV, (a),(d) [110] azimuth, (b),(e) [010] azimuth; STM empty-state images: (c) 100 × 100 nm, $U_s = +1.9$ V, $I_t = 100$ pA; (f) 88 × 88 nm, $U_s = +2.0$ V, $I_t = 100$ pA.